```
L5
     ANSWER 1 OF 28 USPATFULL
AN
       2002:332614 USPATFULL
TI
       Sol-gel method for encapsulating molecules
IN
       Brinker, C. Jeffrey, Albuquerque, NM, United States
       Ashley, Carol S., Albuquerque, NM, United States
       Bhatia, Rimple, Albuquerque, NM, United States
       Singh, Anup K., San Francisco, CA, United States
PA
       Sandia Corporation, Albuquerque, NM, United States (U.S. corporation)
PΙ
       US 6495352
                           В1
                                20021217
ΑI
       US 2000-548638
                                20000413 (9)
PRAI
       US 1999-129771P
                            19990415 (60)
DT
       Utility
FS
       GRANTED
LN.CNT 704
INCL
       INCLM: 435/176.000
       INCLS: 435/007.930; 435/026.000; 435/028.000; 436/527.000; 436/815.000;
              436/829.000
NCL
       NCLM:
              435/176.000
              435/007.930; 435/026.000; 435/028.000; 436/527.000; 436/815.000;
              436/829.000
IC
       [7]
       ICM: C12N011-14
       ICS: G01N033-552; C12Q001-32; C12Q001-28
EXF
       435/7.93; 435/26; 435/28; 435/176; 436/527; 436/815; 436/829
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
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CAS INDEXING IS AVAILABLE FOR THIS PATENT
                                                   ICW: C03C00I-30
                                                                [I]
                                                                        ΣI
                                                106/436.000
                                                              NCTW:
                                                                       NCL
                                                INCTW: 106/436.000
                                                                      INCL
                                                               LN.CNT 2102
                                                       APPLICATION
                                                                        EZ
                                                           Vtilitu
                                                                        DT
                                 (09) EIZI6661
                                                   46050LT-6661 SN
                                20000313 (60)
                                                   US 2000-188761P
                                20000505 (60)
                                                   US 2000-202033P
                                20000710 (60)
                                                   US 2000-216937P
                                                                      IAA9
                             (9) EISI000S
                                            ΙA
                                                    NS 2000-736738
                                                                        IA
                                 20020117
                                            ĮΑ
                                                     US 2002005145
                  Sherman, Jonathan, Franklin, TW, UNITED STATES
                                                                        Ιđ
                                                                       NI
                                       production and use thereof
Nanoparticulate titanium dioxide coatings, and processes for the
                                                                       IJ
                                            2002:10777 USPATFULL
                                                                       ИA
                                          ANSWER 5 OF 28 USPATFULL
                                                                       SI
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JP 1989-217124
                               19890823
       JP 1989-218054
                               19890824
       JP 1989-229694
                               19890905
       JP 1989-238295
                               19890913
       JP 1989-238296
                               19890913
IC
       ICM C03C017-25
       TCS
           C03C017-36
                           G02B001-10
                                         . H01J001-64
                                                          H01J029-22
            C09D001-04
GRANTED PATENT - ERTEILTES PATENT - BREVET DELIVRE
       391226 EUROPATFULL UP 20011005 EW 199428 FS PS STA B
AN
TIEN
       Method for manufacturing layer-built material with silicon dioxide film
       containing organic colorant and the layer-built material manufactured
TIDE
       Verfahren zur Herstellung eines schichtfoermig aufgebauten Materials mit
       einem organischen Farbstoff enthaltenden Siliziumdioxidfilm sowie das
       somit erzeugte Produkt.
       Procede pour la preparation d'un materiel stratifie avec un film de
TIFR
       silice contenant un colorant organique et le materiel stratifie ainsi
       produit.
       Takemura, Kazuo, 12-18, Nogami 6-chome, Takarazuka-shi, Hyogo-ken, JP;
IN
       Ino, Jyuichi, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, JP;
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Kawahara, Hideo, 8-2-312 Makiochi 5-chome, Mino-shi, Osaka-fu, JP; Kitaoka, Masaki, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, NIPPON SHEET GLASS CO. LTD., 5-11, Doshomachi 3-chome, Chuo-ku Osaka-shi PA Osaka-fu, JP SO Wila-EPS-1994-H28-T1 DS R DE; R FR; R GB; R IT; R NL PIT EPB1 EUROPAEISCHE PATENTSCHRIFT PI · EP 391226 B1 19940713 OD 19901010 ΑI EP 1990-105873 19900328 PRAI JP 1989-83816 19890401 JP 1989-167366 19890629 JP 1989-167367 19890629 JP 1989-167368 19890629 JP 1989-204214 19890807 JP 1989-217124 19890823 JP 1989-218054 19890824 JP 1989-229694 19890905 JP 1989-238295 19890913 JP 1989-238296 19890913 REP GB 626810 GB 2018621 REN

D. AVNIR, V. KAUFMAN and R. REISFELD, J. Noncryst. Solids 74 (1985), 395 - 406. T. TANI, Ceramics 21 (1986), No. 2, 111 - 118. PATENT ABSTRACTS OF JAPAN, unexamined applications, C field, vol. 11, no. 141, May 8, 1987 THE PATENT OFFICE JAPANESE GOVERNMENT page 76 C 421 PATENT ABSTRACTS OF JAPAN, unexamined applications, C field, vol. 10, no. 23, January 29, 1986 THE PATENT OFFICE JAPANESE GOVERMENT page 96 C 325 ICM C03C017-25

ICS C03C017-36 G02B001-10 H01J001-64 H01J029-22 C09D001-04

=>

```
Suita-shi, Osaka-fu, JP;
       Hikawa, Tetsuo, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
       Suita-shi, Osaka-fu, JP;
       Takata, Akira, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
       Suita-shi, Osaka-fu, JP;
       Ukai, Yukihiro, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
       Suita-shi, Osaka-fu, JP;
       Sawada, Takashi, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
       Suita-shi, Osaka-fu, JP;
       Asakawa, Toshifumi, 6-9-25, Tsukimino, Yamatoshi, Kanagawa, JP
       MEGA CHIPS CORPORATION, 1-12-38, Esaka-cho, Suita-shi, Osaka-fu, JP;
PA
       Crystal Device Corporation, 15-16, Machikaneyama-cho, Toyonaka-shi,
       Osaka-fu, JP
SO
       Wila-EPZ-1995-H26-T1a
       R DE; R FR; R GB; R NL
DS
       EPA2 EUROPAEISCHE PATENTANMELDUNG
PIT
                            A2 19950628
PΤ
       EP 659910
                               19950628
OD
                               19941118
ΑI
       EP 1994-118223
                               19931119
PRAI
       JP 1993-314147
       JP 1993-314470
                               19931119
                               19931122
       JP 1993-316108
       JP 1993-341322
                                19931210
       JP 1993-345314
                               19931220
       JP 1993-350297
                               19931227
       JP 1993-354139
                               19931228
       JP 1994-15505
                                19940209
IC
       ICM C30B025-00
           C23C016-48
       ICS
L3
       ANSWER 6 OF 6 EUROPATFULL COPYRIGHT
PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET
       391226 EUROPATFULL ED 20000903 EW 199041 FS OS STA B
.AN
       Method for manufacturing layer-built material with silicon dioxide film
TIEN
       containing organic colorant and the layer-built material manufactured
       Verfahren zur Herstellung eines schichtfoermig aufgebauten Materials mit
TIDE
       einem organischen Farbstoff enthaltenden Siliziumdioxidfilm sowie das
       somit erzeugte Produkt.
       Procede pour la preparation d'un materiel stratifie avec un film de
TIFR
       silice contenant un colorant organique et le materiel stratifie ainsi
       Takemura, Kazuo, 12-18, Nogami 6-chome, Takarazuka-shi, Hyogo-ken, JP;
IN
       Ino, Juichi, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, JP;
       Kawahara, Hideo, 8-2-312 Makiochi 5-chome, Mino-shi, Osaka-fu, JP;
       Kitaoka, Masaki, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken,
       JΡ
       NIPPON SHEET GLASS CO. LTD., 5-11, Dosho-machi 3-chome, Chuo-ku
PA
       Osaka-shi Osaka, JP
       Wila-EPZ-1990-H41-T1
SO
       R DE; R FR; R GB; R IT; R NL
DS
```

EPA1 EUROPAEISCHE PATENTANMELDUNG

A1 19901010

19901010

19900328

19890401

19890629

19890629

19890807

19890629

PIT

PI.

OD

ΑI

PRAI

EP 391226

EP 1990-105873

JP 1989-167366

JP 1989-167367

JP 1989-167368 JP 1989-204214

JP 1989-83816

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EPA1 EUROPAEISCHE PATENTANMELDUNG
PIT
                            Al 19970326
       EP 764992
PΙ
                               19970326
OD
                               19960918
       EP 1996-114974
ΑI
PRAI
       JP 1995-240372
                               19950919
       JP 1995-322670
                               19951212
       JP 1996-190848
                                19960719
                                19960917
       JP 1996-245353
       ICM H01L041-09
TC
            H01L041-24
                           B41J002-045
       ICS
GRANTED PATENT - ERTEILTES PATENT - BREVET DELIVRE
       764992 EUROPATFULL UP 20000903 EW 200034 FS PS
AN
       Thin piezoelectric film element, process for the preparation thereof and
TIEN
       ink jet recording head using thin piezoelectric film element.
       Piezoelektrisches Duennschichtelement, Verfahren zum Herstellen und
TIDE
       dieses piezoelektrisches Duennschichtelement verwendender
       Tintenstrahldruckkopf.
       Element a couche mince piezoelectrique, procede de fabrication, et tete
TIFR
       d'enregistrement a jet d'encre utilisant cet element a couche mince
       piezoelectrique.
       Shimada, Masato, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
IN
       Nagano, JP;
       Takahashi, Tetsushi, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
       Nagano, JP;
       Kamei, Hiroyuki, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
       Nagano, JP;
       Qui, Hong, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi, Nagano, JP
       SEIKO EPSON CORPORATION, 4-1, Nishishinjuku 2-chome, Shinjuku-ku Tokyo,
PA
       Wila-EPS-2000-H34-T2
SO
DS
       R DE; R FR; R GB; R IT
PIT
       EPB1 EUROPAEISCHE PATENTSCHRIFT
                             B1 20000823
PΤ
       EP 764992
                                19970326
OD
                                19960918
       EP 1996-114974
AΙ
                                19950919
PRAI
       JP 1995-240372
                                19951212
       JP 1995-322670
       JP 1996-190848
                                19960719
                                19960917
       JP 1996-245353
                                US 5198269 A
REP
       EP 656665
       VASSANT KUMAR ET AL.: "Lead zirconate titanate films by rapid thermal
REN
       processing", APPLIED PHYSICS LETTERS,, 18. March 1991, vol. 58, no. 11,
       pages 1161 to 1163
       ICM H01L041-09
IC
                            B41J002-045
       ICS H01L041-24
                                               2003 WILA
       ANSWER 5 OF 6 EUROPATFULL COPYRIGHT
PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET
```

659910 EUROPATFULL ED 19991205 EW 199526 FS OS

Suita-shi, Osaka-fu, JP;

Semiconductor device and method of fabricating the same.

Halbleiter-Vorrichtung und Verfahren zu deren Herstellung.

Dispositif semi-conducteur et procede pour fabriquer celui-ci.

Shiindo, Masahiro, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,

Kosaka, Daisuke, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,

JP

SO DS

AN

TIEN

TIDE

TIFR

IN

Wila-EPZ-1997-H13-T2b

R DE; R FR; R GB; R IT

```
JP 1990-156482
PRAI
DT
      Utility
      Granted
FS
LN.CNT 785
INCL
       INCLM: 427/277.000
       INCLS: 427/162.000; 427/278.000; 427/294.000; 427/359.000; 427/385.500
NCL
              427/277.000
              427/162.000; 427/278.000; 427/294.000; 427/359.000; 427/385.500
      NCLS:
       [5]
IC
       ICM: B05D005-00
       427/162; 427/164; 427/165; 427/294; 427/296; 427/385.5; 427/355;
EXF
       427/277; 427/278; 427/258; 427/359; 427/370; 427/371
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
    ANSWER 3 OF 6 USPATFULL
L3
       93:24745 USPATFULL
AN
       Process for making sol-gel deposited ferroelectric thin films
TI
       insensitive to their substrates
       Swartz, Scott L., Dublin, OH, United States
TN
      Melling, Peter J., Worthington, OH, United States
       Battelle Memorial Institute, Columbus, OH, United States (U.S.
PA
       corporation)
                               19930330
       US 5198269
PΙ
                               19890828 (7)
       US 1989-399724
ΑI
       Continuation-in-part of Ser. No. US 1989-342272, filed on 24 Apr 1989,
RLI
       now abandoned
DT
       Utility
       Granted
FS
LN.CNT 1323
INCL
       INCLM: 427/226.000
       INCLS: 427/126.200; 427/126.300; 427/419.300; 427/419.200; 427/379.000;
              427/380.000
              427/226.000
NCL
       NCLM:
              427/126.200; 427/126.300; 427/379.000; 427/380.000; 427/419.200;
       NCLS:
              427/419.300
IC
       ICM: B05D003-02
       427/419.3; 427/126.2; 427/126.3; 427/100; 427/62; 427/63; 427/226;
EXF
       427/419.2; 427/379; 427/380; 505/734; 505/735
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
       ANSWER 4 OF 6 EUROPATFULL COPYRIGHT 2003 WILA
PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET
       764992 EUROPATFULL ED 19970421 EW 199713 FS OS
       Thin piezoelectric film element, process for the preparation thereof and
TIEN .
       ink jet recording head using thin piezoelectric film element.
       Piezoelektrisches Duennschichtelement, Verfahren zum Herstellen und
TIDE
       dieses piezoelektrische Duennschichtelement verwendender
       Tintenstrahldruckkopf.
       Element a couche mince piezoelectrique, procede de fabrication, et tete
TIFR
       d'enregistrement a jet d'encre utilisant cet element a couche mince
       piezoelectrique.
       Shimada, Masato, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
IN
       Nagano, JP;
       Takahashi, Tetsushi, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
       Nagano, JP;
       Kamei, Hiroyuki, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
       Nagano, JP;
       Qui, Hong, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi, Nagano, JP
       SEIKO EPSON CORPORATION, 4-1, Nishishinjuku 2-chome, Shinjuku-ku Tokyo,
PA
```

19900614

```
3 FILES SEARCHED...
   6 FILES SEARCHED...
           401 L1 AND (SURFACE OR SUBSTRATE)
=> s 12 and (melt or heat) (p) distortion
             6 L2 AND (MELT OR HEAT) (P) DISTORTION
=> s (12 or 13) and (Antibacterial or microbiocid? or antimicrobial or silver)
            77 (L2 OR L3) AND (ANTIBACTERIAL OR MICROBIOCID? OR ANTIMICROBIAL
                OR SILVER)
=> s (11 or 12 or 13 or 14) and bath(4p)(pH or basic or caustic)
            28 (L1 OR L2 OR L3 OR L4) AND BATH(4P) (PH OR BASIC OR CAUSTIC)
=> s (11-15) and Klebsiella
             O ((L1 OR L2 OR L3 OR L4 OR L5)) AND KLEBSIELLA
=> s (l1 or l2) and klebsiella
             0 (L1 OR L2) AND KLEBSIELLA
=> s (11-5) and modified plate
   4 FILES SEARCHED...
             O ((L1 OR L2 OR L3 OR L4 OR L5)) AND MODIFIED PLATE
r_8
=> dup rem 15
PROCESSING COMPLETED FOR L5
             28 DUP REM L5 (0 DUPLICATES REMOVED)
=> d 13 1-6
    ANSWER 1 OF 6 USPATFULL
1.3
       2002:256840 USPATFULL
AN
       Lamp utilizing fiber for enhanced starting field
TI
       Golkowski, Czeslaw, Ithaca, NY, UNITED STATES
IN
       Hammer, David, Ithaca, NY, UNITED STATES
       Song, Byungmoo, Ithaca, NY, UNITED STATES
       Tian, Yonglai, Fairfax, VA, UNITED STATES
       Cekic, Miodrag, Bethesda, MD, UNITED STATES
       Ury, Michael G., Great Barrington, MA, UNITED STATES
       Kirkpatrick, Douglas A., Great Falls, VA, UNITED STATES
                                20021003
PΙ
       US 2002140381
                          A1
                                20010420 (9)
                          A1
ΑI
       US 2001-838234
                            20000426 (60)
       US 2000-199810P
PRAI
DΨ
       Utility
       APPLICATION
FS .
LN.CNT 1083
       INCLM: 315/363.000
INCL
       NCLM: 315/363.000
NCL
IC
        [7]
        ICM: H05B041-16
     ANSWER 2 OF 6 USPATFULL
L3
        93:65190 USPATFULL
AN
        Process for producing a minute-patterned substrate
TI
        Matsuno, Yoshihiro, Tsukuba, Japan
IN
        Matsuda, Atsunori, Tsukuba, Japan
       Katayama, Shinya, Tsukuba, Japan
       Nippon Sheet Glass Co., Ltd., Osaka, Japan (non-U.S. corporation)
 PA
                                19930810
ΡI
        US 5234717
                                19921019 (7)
        US 1992-963035
ΑI
        Continuation of Ser. No. US 1991-713799, filed on 12 Jun 1991, now
 RLI
        abandoned
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